



STD45NF75

N-channel 75 V, 0.018 Ω , 40 A DPAK
STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STD45NF75	75 V	< 0.024 Ω	40 A ⁽¹⁾

1. Current limited by package

- 100% avalanche tested
- Gate charge minimized

Application

- Switching applications

Description

This Power MOSFET is the latest development of STMicroelectronics's unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

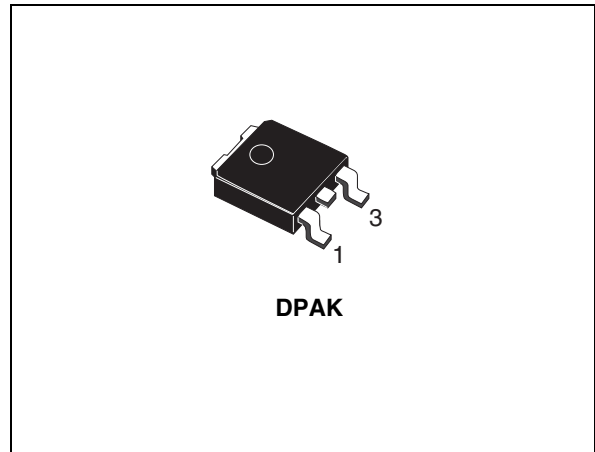


Figure 1. Internal schematic diagram

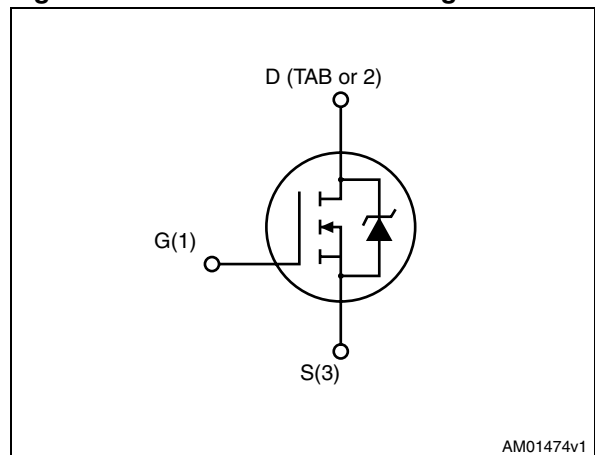


Table 1. Device summary

Order code	Marking	Package	Packaging
STD45NF75T4	D45NF75	DPAK	Tape and reel

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Spice thermal model** 10

4 **Test circuits** 11

5 **Package mechanical data** 12

6 **Packing mechanical data** 14

7 **Revision history** 15



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	75	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	75	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	40	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	30	A
$I_{DM}^{(2)}$	Drain current (pulsed)	160	A
P_{tot}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	125	W
	Derating factor	0.83	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	20	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	500	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Current limited by package
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 40\text{ A}$, $di/dt \leq 800\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
4. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 20\text{ A}$, $V_{DD} = 40\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.2	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max	see Figure 16. and Figure 17.	$^\circ\text{C}/\text{W}$
T_J	Maximum lead temperature for soldering purpose ⁽¹⁾	260	$^\circ\text{C}$

1. for 10 sec. 1.6 mm from case

2 Electrical characteristics

($T_{CASE}=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	75			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, $T_C = 125\text{ }^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$		0.018	0.024	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 25\text{ V}$, $I_D = 20\text{ A}$	-	50		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1760 360 140		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 37\text{ V}$, $I_D = 20\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 20)	-	15 40 55 12		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 60\text{ V}$, $I_D = 40\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$ (see Figure 21)	-	60 13 23	80	nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		40 160	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 40\text{ A}$, $V_{DD} = 30\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^{\circ}\text{C}$ (see Figure 22)	-	120 410 7.5		ns nC A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

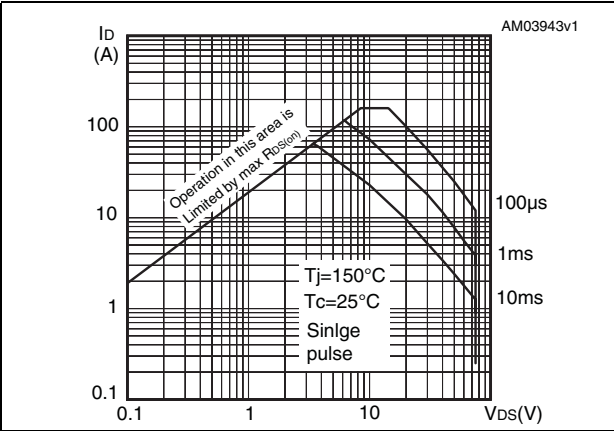


Figure 3. Thermal impedance

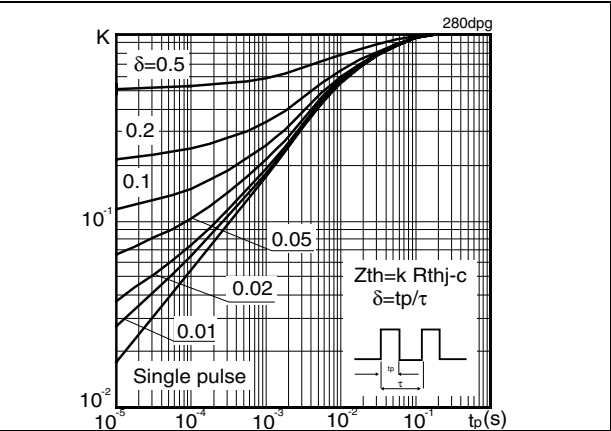


Figure 4. Output characteristics

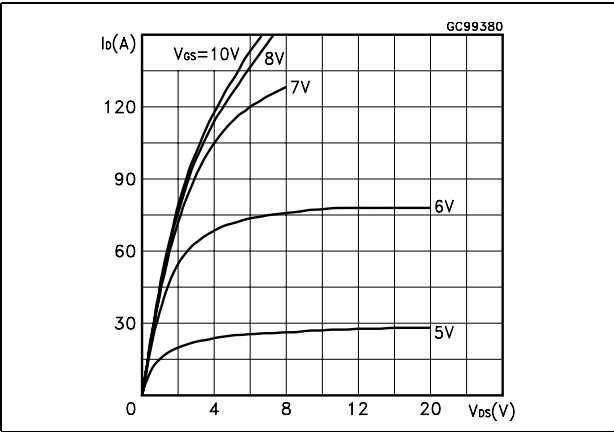


Figure 5. Transfer characteristics

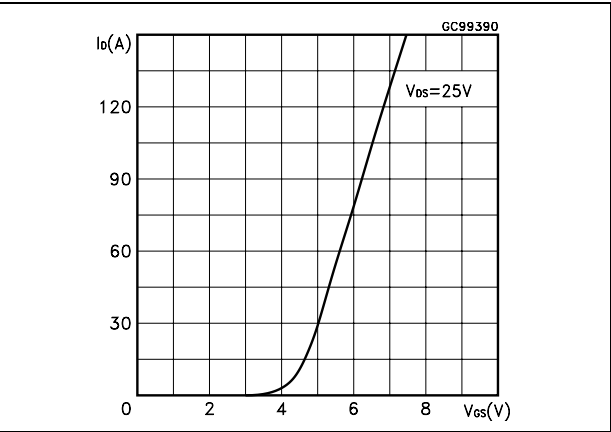


Figure 6. Transconductance

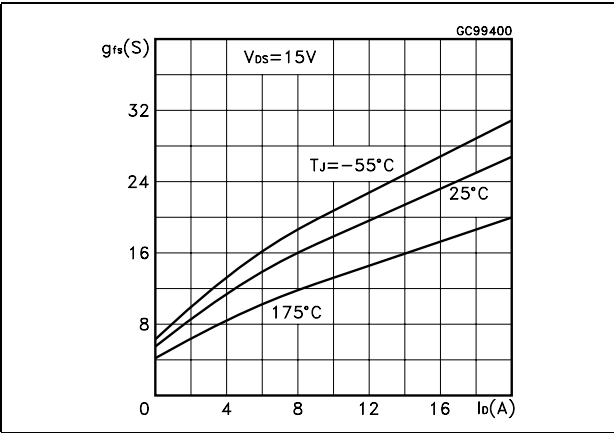


Figure 7. Static drain-source on resistance

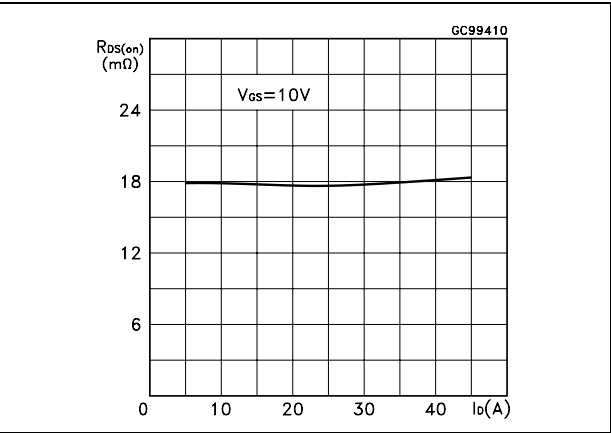


Figure 8. Gate charge vs. gate-source voltage

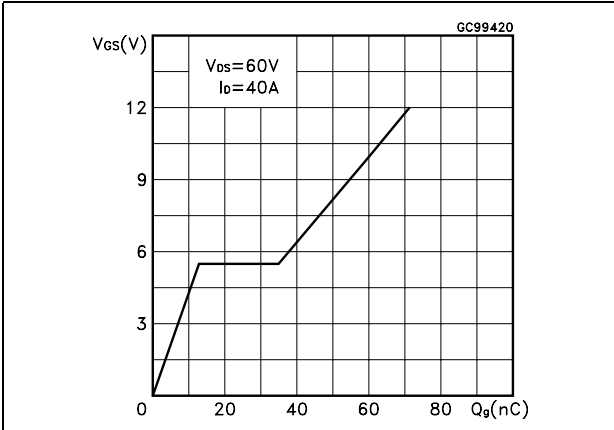


Figure 9. Capacitance variations

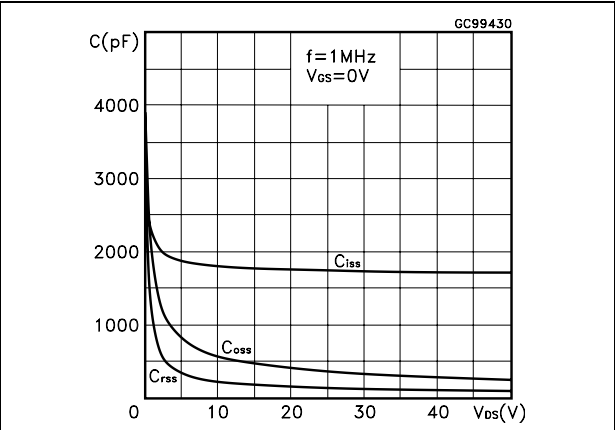


Figure 10. Normalized gate threshold voltage vs. temperature

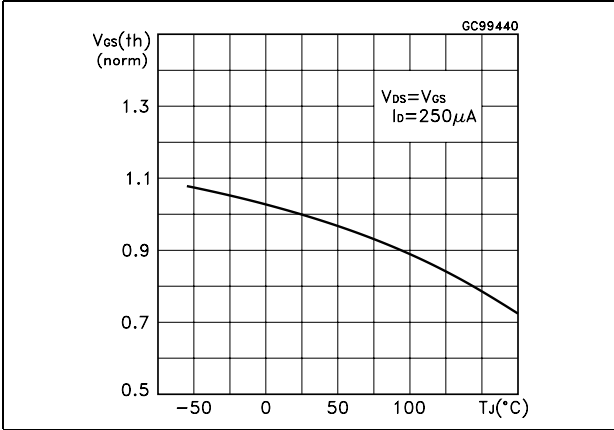


Figure 11. Normalized on resistance vs. temperature

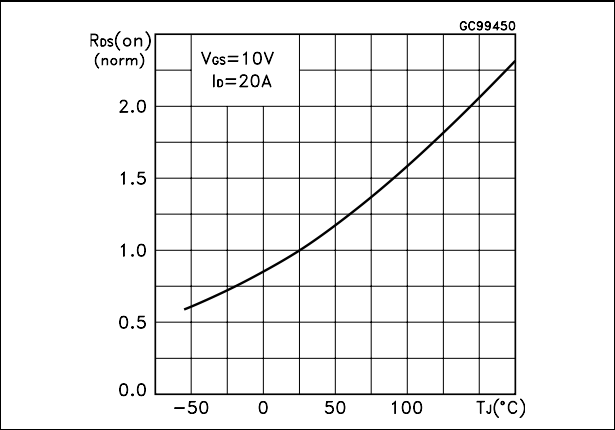


Figure 12. Source-drain diode forward characteristics

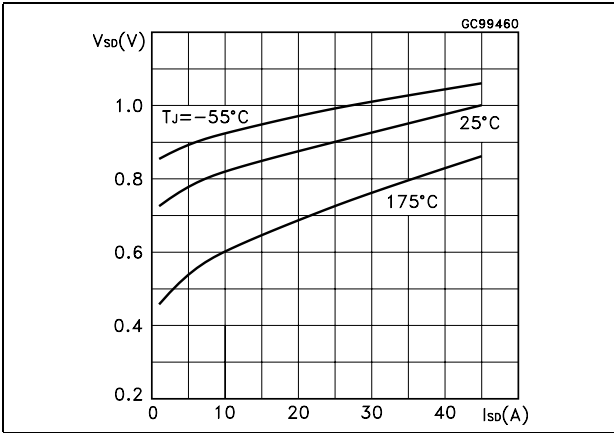


Figure 13. Normalized breakdown voltage vs. temperature

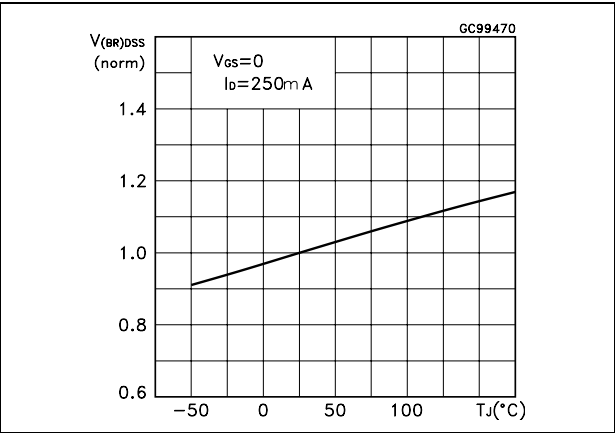


Figure 14. Power derating vs. Tj

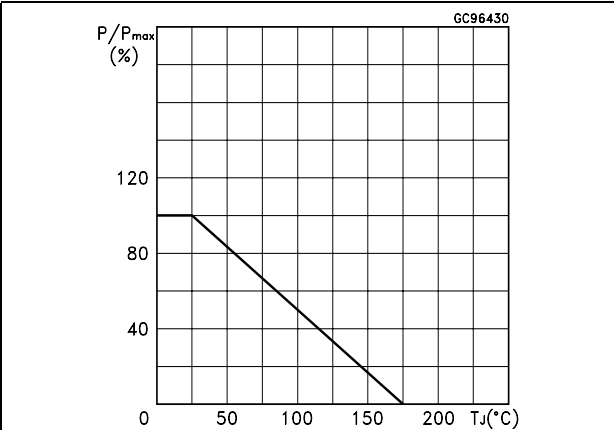


Figure 15. Max Id current vs. Tc

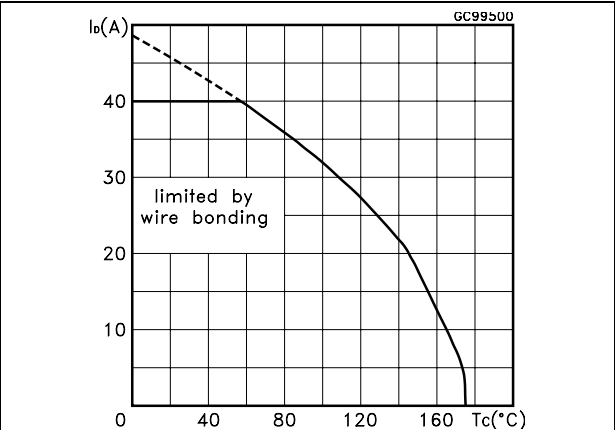


Figure 16. Thermal resistance Rthj-a vs. pcb copper area

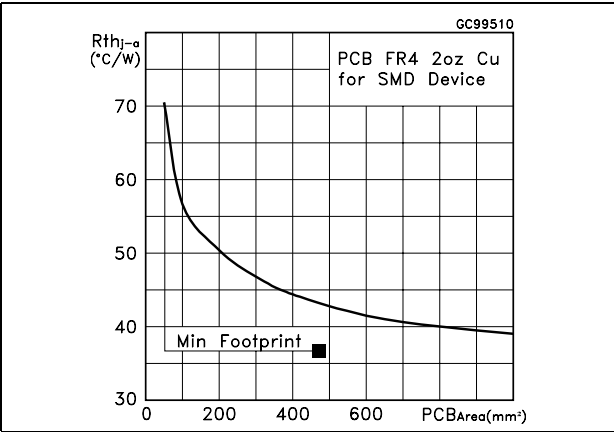


Figure 17. Max power dissipation vs. pcb copper area

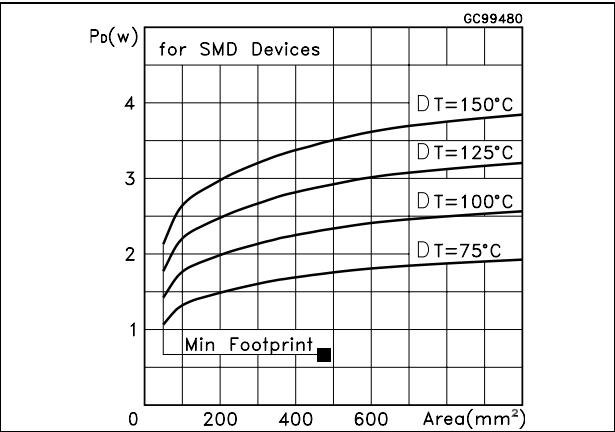
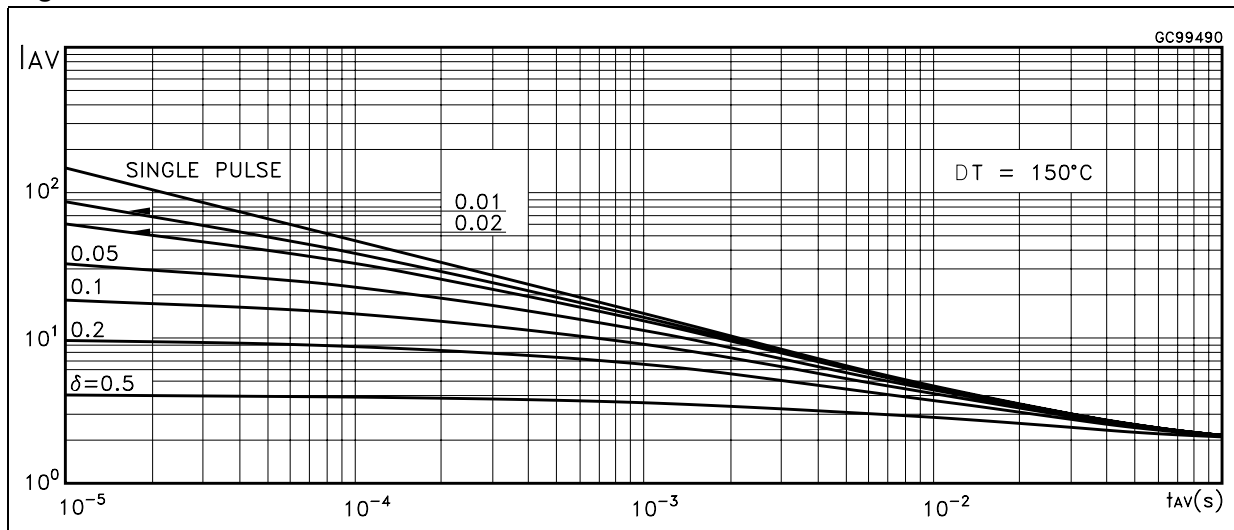


Figure 18. Allowable I_{AV} vs. time in avalanche

The previous curve gives the safe operating area for unclamped inductive loads, single pulse or repetitive, under the following conditions:

$$P_{D(AVE)} = 0.5 * (1.3 * B_{VDSS} * I_{AV})$$

$$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$$

Where:

I_{AV} is the allowable current in avalanche

$P_{D(AVE)}$ is the average power dissipation in avalanche (single pulse)

t_{AV} is the time in avalanche

To de rate above 25°C , at fixed I_{AV} , the following equation must be applied:

$$I_{AV} = 2 * (T_{jmax} - T_{CASE}) / (1.3 * B_{VDSS} * Z_{th})$$

Where:

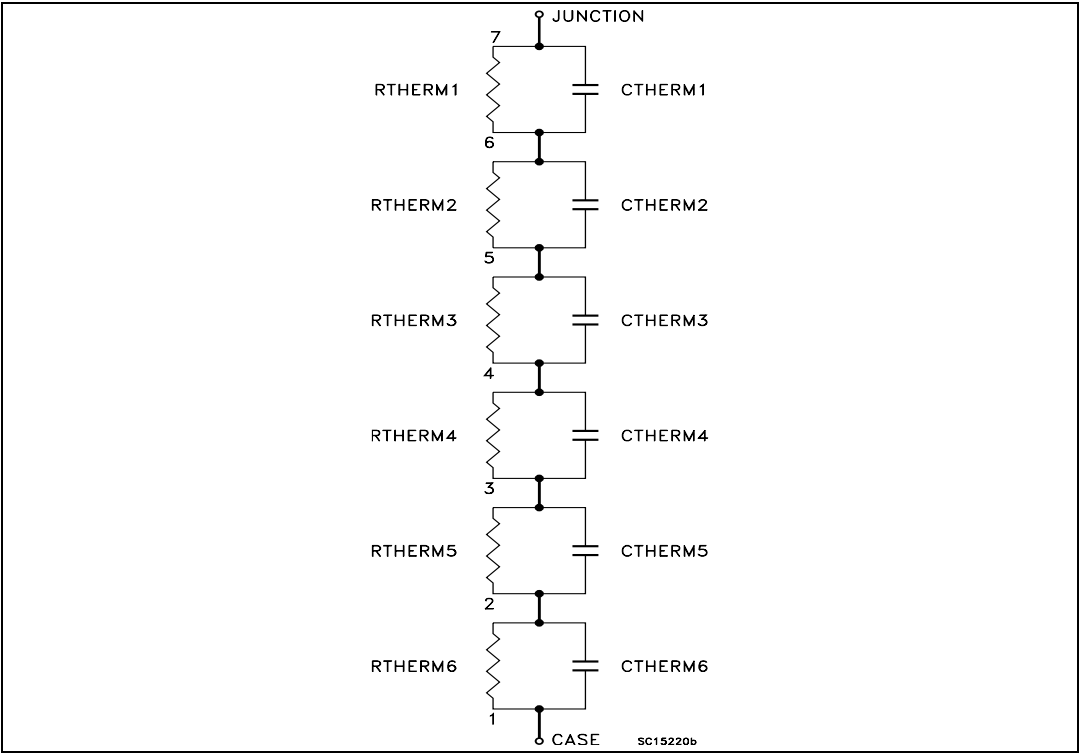
$Z_{th} = K * R_{th}$ is the value coming from normalized thermal response at fixed pulse width equal to T_{AV} .

3 Spice thermal model

Table 7. Spice parameter

Parameter	Node	Value
CTHERM1	7 - 6	$6 * 10^{-4}$
CTHERM2	6 - 5	$8 * 10^{-3}$
CTHERM3	5 - 4	$2 * 10^{-2}$
CTHERM4	4 - 3	$6 * 10^{-2}$
CTHERM5	3 - 2	$9.65 * 10^{-2}$
CTHERM6	2 - 1	$6 * 10^{-1}$
R THERM1	7 - 6	0.045
R THERM2	6 - 5	0.105
R THERM3	5 - 4	0.150
R THERM4	4 - 3	0.225
R THERM5	3 - 2	0.375
R THERM6	2 - 1	0.600

Figure 19. Thermal network



4 Test circuits

Figure 20. Switching times test circuit for resistive load

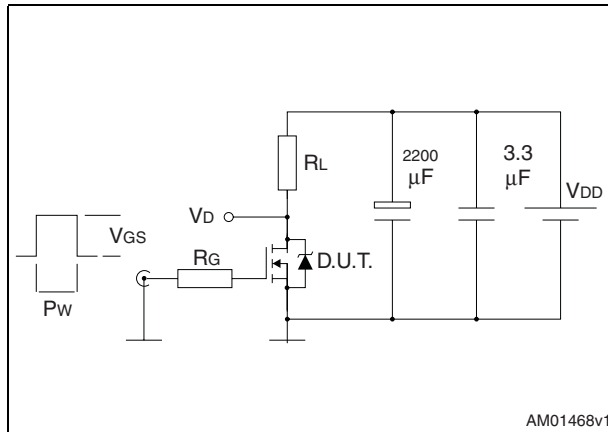


Figure 21. Gate charge test circuit

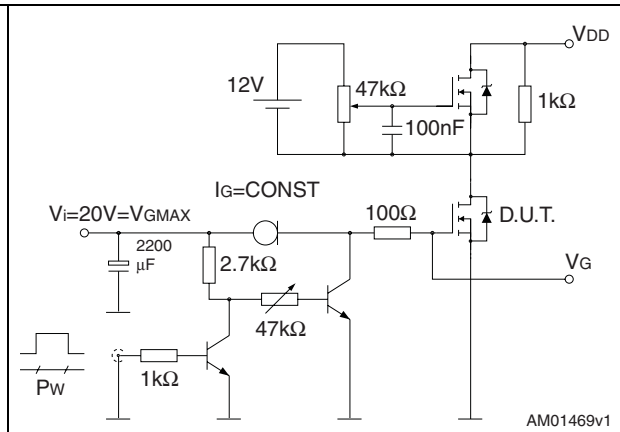


Figure 22. Test circuit for inductive load switching and diode recovery times

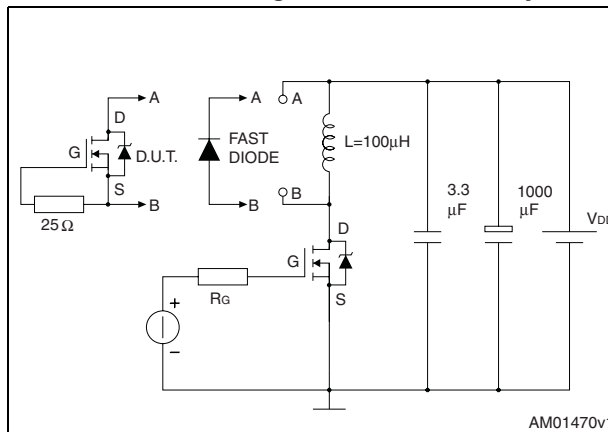


Figure 23. Unclamped inductive load test circuit

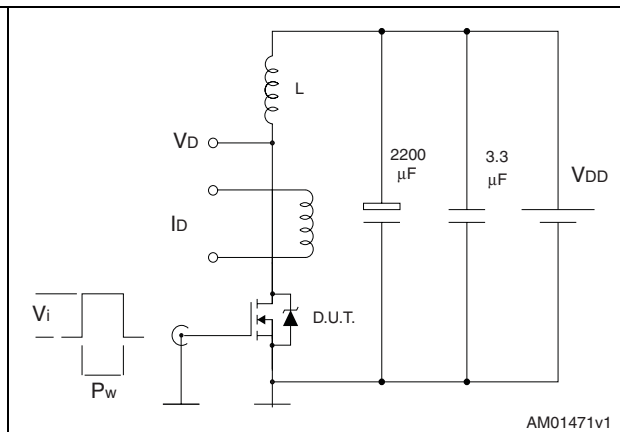


Figure 24. Unclamped inductive waveform

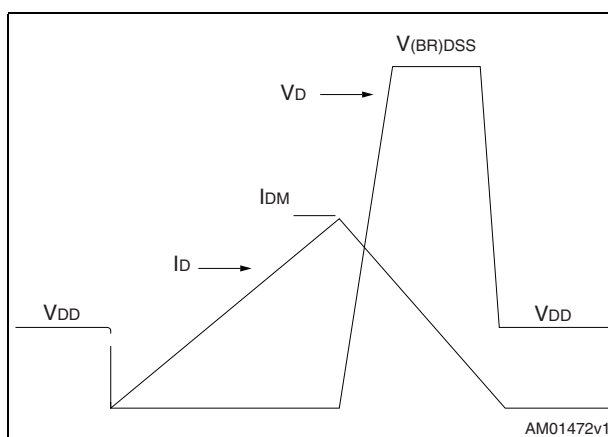
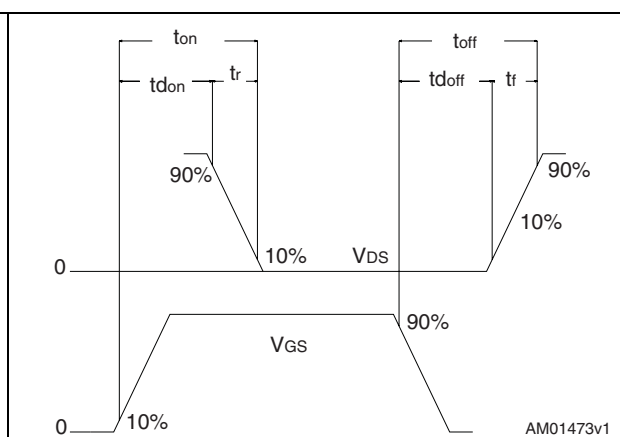


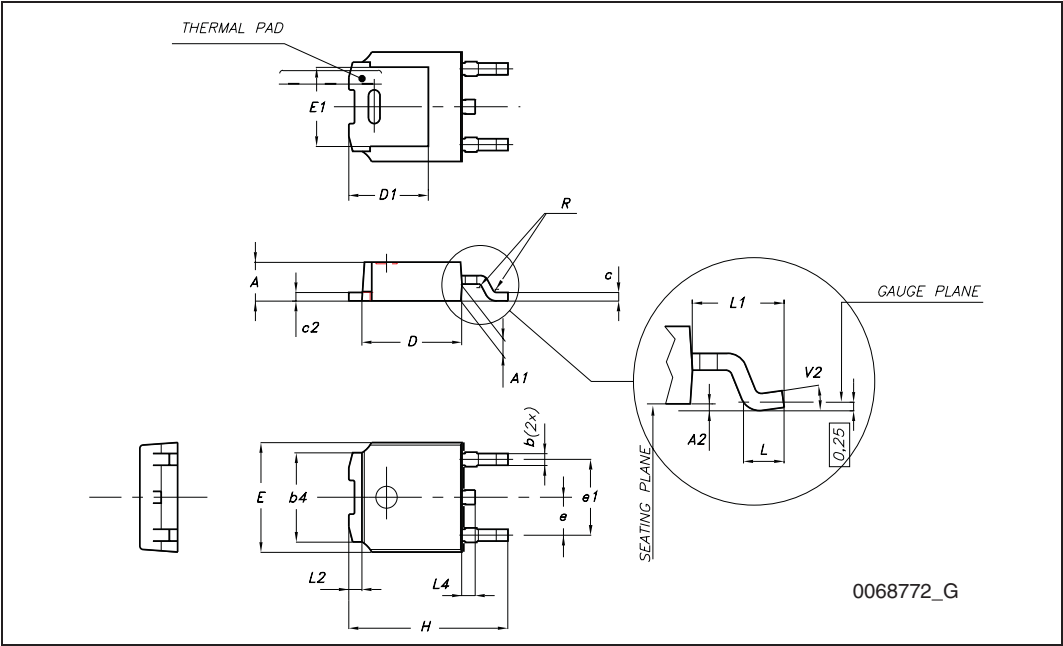
Figure 25. Switching time waveform



5 **Package mechanical data**

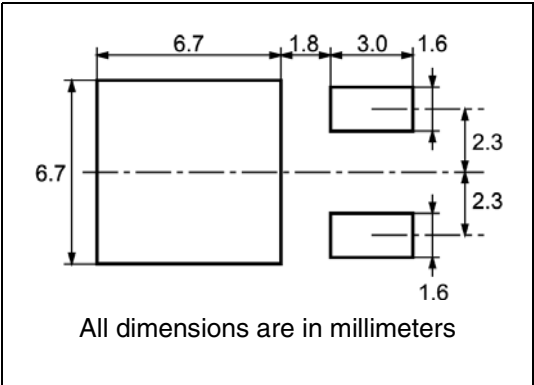
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TO-252 (DPAK) mechanical data			
DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

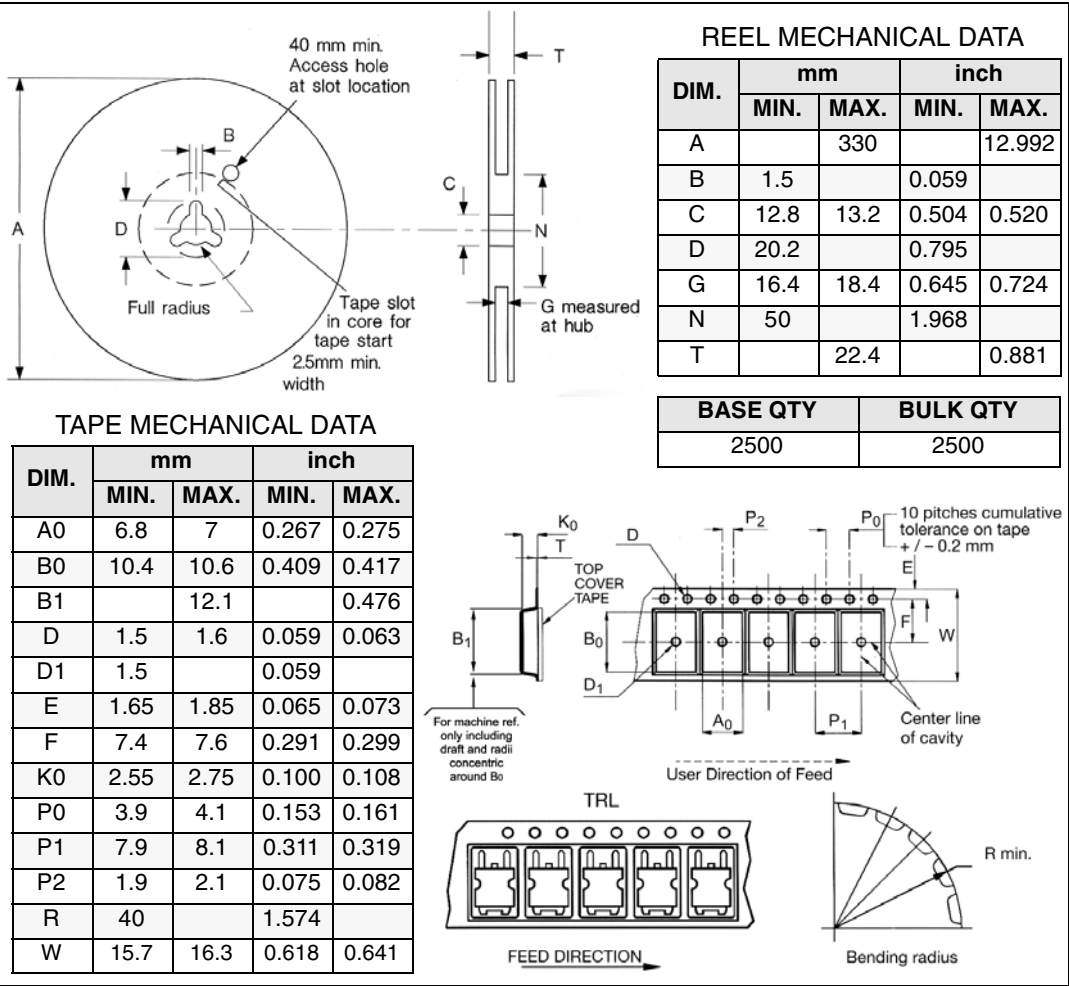


6 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



7 Revision history

Table 8. Document revision history

Date	Revision	Changes
22-Jun-2004	1	Preliminary version
09-Sep-2004	2	Complete version
11-Jul-2006	3	New template, no content change
20-Feb-2007	4	Typo mistake on page 1
20-May-2009	5	<i>Figure 2</i> and <i>Figure 3</i> have been updated

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